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With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

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Dual P-Channel 20-V (D-S) MOSFET

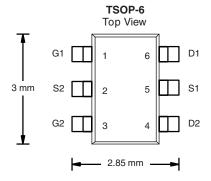
PRODUCT SUMMARY			
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)	
- 20	0.145 at V _{GS} = - 4.5 V	- 2.2	
	0.200 at V _{GS} = - 2.5 V	- 1.8	
	0.300 at V _{GS} = - 1.8 V	- 1.5	

FEATURES

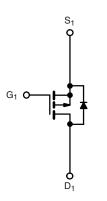
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFETs: 1.8 V Rated
- Compliant to RoHS Directive 2002/95/EC



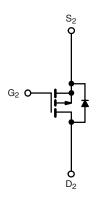
FREE



Ordering Information: Si3911DV-T1-E3 (Lead (Pb)-free) Si3911DV-T1-GE3 (Lead (Pb)-free and Halogen-free)







P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	$T_A = 25 ^{\circ}C$, unles	ss otherwise r	noted		
Parameter		Symbol	5 s	Steady State	Unit
Drain-Source Voltage		V_{DS}	- 20		V
Gate-Source Voltage		V _{GS}	± 8		
Continuous Drain Current /T 150 °C\8	T _A = 25 °C	- I _D	- 2.2	- 1.8	
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		- 1.8	- 1.5	
Pulsed Drain Current		I _{DM}	± 8		Α
Continuous Diode Current (Diode Conduction) ^a		I _S	- 1.05	- 0.75	
Maximum Power Dissipation ^a	T _A = 25 °C	- P _D	1.15	0.83	W
	T _A = 70 °C	гD	0.73	0.53	VV
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Marrian Institut to Ambient	t ≤ 5 s	- R _{thJA}	93	110	°C/W
Maximum Junction-to-Ambient ^a	Steady State		130	150	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	90	90	

Notes: a. Surface Mounted on 1" x 1" FR4 board.

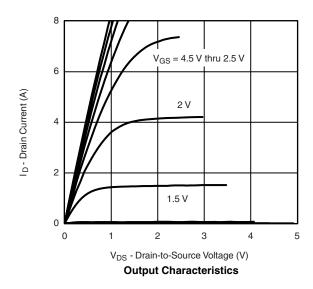
Vishay Siliconix

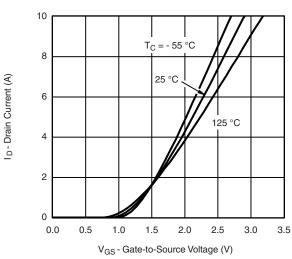


SPECIFICATIONS T _J = 25 °C, unless otherwise noted								
Parameter	Symbol	Test Conditions Min.		Тур.	Max.	Unit		
Static								
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250 \mu A$	- 0.45			V		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			± 100	nA		
Zava Cata Valtaga Dvain Current	1	V _{DS} = - 16 V, V _{GS} = 0 V			- 1			
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 16 V, V _{GS} = 0 V, T _J = 85 °C			- 10	μΑ		
On-State Drain Current ^a	I _{D(on)}	V _{DS} = - 5 V, V _{GS} = - 4.5 V	- 5			Α		
		$V_{GS} = -4.5 \text{ V}, I_D = -2.2 \text{ A}$		0.115	0.145			
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = -2.5 \text{ V}, I_D = -1.8 \text{ A}$		0.163	0.200	Ω		
		V _{GS} = - 1.8 V, I _D = - 1.0 A		0.240	0.300			
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 5 V, I _D = - 2.2 A		5		S		
Diode Forward Voltage ^a	V_{SD}	$I_S = -1.05 \text{ A}, V_{GS} = 0 \text{ V}$		- 0.8	- 1.1	V		
Dynamic ^b								
Total Gate Charge	Q_g			5	7.5			
Gate-Source Charge	Q _{gs}	Q_{gs} $V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_D = -2.2 \text{ A}$		1		nC		
Gate-Drain Charge	Q_{gd}			0.9				
Turn-On Delay Time	t _{d(on)}			12	20			
Rise Time	t _r	V_{DD} = - 4 V, R_L = 8 Ω		29	50			
Turn-Off Delay Time	t _{d(off)}	$\text{I}_\text{D}\cong$ - 1 A, V_GEN = - 4.5 V, R_g = 6 Ω		24	45	ns		
Fall Time	t _f			30	50			
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 1.05 A, dI/dt = 100 A/μs		20	40			

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





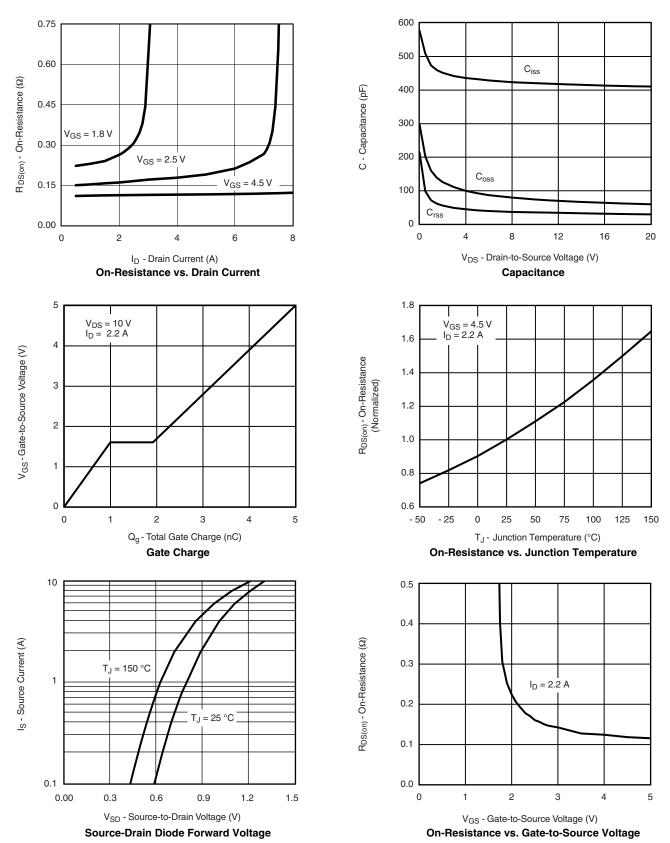
Notes: a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %. b. Guaranteed by design, not subject to production testing.







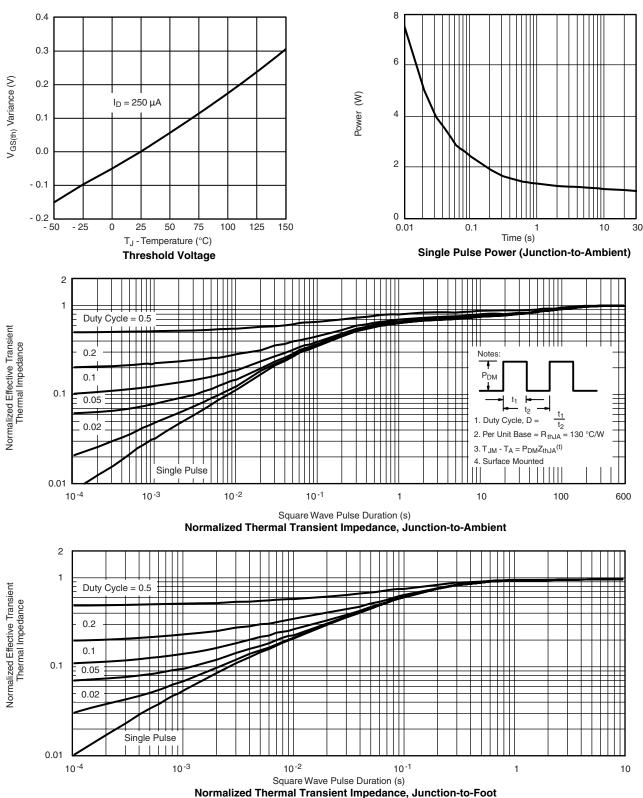
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Vishay Siliconix

VISHAY.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppq?71380.



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Vishay

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